

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: Not yet assigned
Applicants: Christian DUSSARRAT, et al.
Filed Internationally: April 8, 2004
US National: Herewith
Title: METHODS FOR PRODUCING SILICON NITRIDE FILMS BY
VAPOR-PHASE GROWTH
TC/A.U: Unknown
Examiner: Unknown
Docket No.: Serie 6070
Customer No.: 000040582

INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents
P.O. Box 1450
Washington, D.C. 20231

Dear Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the non-US patent documents cited on the enclosed PTO Form 1449 is enclosed.

No fee is due at this time in accordance with 37 C.F.R. § 1.97. However, the Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17 and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 01-1375. This paper is submitted in duplicate.

Respectfully submitted,

Date: **October 17, 2005**



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INFORMATION DISCLOSURE CITATION (USE SEVERAL SHEETS IF NECESSARY)				ATTY. DOCKET NO. Serie 6070		SERIAL NO. Not yet assigned 10/553573	
				APPLICANT(S) Christian DUSSARRAT, et al.			
				FILING DATE Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
	A1	US 2001 024867	09/27/2001	Saida et al.			
	A2	US 2001 048973	12/06/2001	Sato et al.			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	B1	EP 1 441 042	07/28/2004	Europe			
	B2	GB 1 006 803	10/06/1965	United Kingdom			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	C1		International Search Report for PCT/IB04/001346				
	C2		Smirnova T. P., et al.: "SiCN alloys obtained by remote plasma chemical vapour deposition from novel precursors", Preparation and Characterization, Elsevier Sequoia, NL, vol. 429, no. 1-2, April 1, 2003, pp. 144-151				
	C3		Grow, J. M., et al., "Growth kinetics and characterization of low pressure chemically vapor deposited Si ₃ N ₄ films from (C ₄ H ₉) ₂ SiH ₂ and NH ₃ ", Materials Letters, vol. 23, 1995, pp. 187-193				
	C4		Levy, R. A., et al., "Low pressure chemical vapor deposition of silicon nitride using the environmentally friendly tris(dimethylamino)silane precursor", M. Mater. Res., vol. 11, no. 6, June 1996, pp. 1483-1488				
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							